

L Number	Hits	Search Text	DB	Time stamp
1	7756671	via or opening or trench or v-trench or groove or v-groove or contact or recess or cavity or cavities or hole or damascene	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 09:08
2	289	(via or opening or trench or v-trench or groove or v-groove or contact or recess or cavity or cavities or hole or damascene) and 216/37	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 09:10
3	12	((via or opening or trench or v-trench or groove or v-groove or contact or recess or cavity or cavities or hole or damascene) and 216/37) and 438/734	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:05
5	0	438/638.ccls. with (oxygen or o2 or osub2 or "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:06
6	1646	438/637.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:06
7	0	438/637.ccls. with (oxygen or o2 or osub2 or "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 10:06
4	543	438/638.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:27
8	21	photoresist with low-k with (spin-on polymer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:39
9	15	photoresist with (spin-on adj polymer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:42
10	742	photoresist with (low-k or (low adj dielectric) or silk or flare or (organic adj (ild dielectric interlayer)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:51
11	79	(photoresist with (low-k or (low adj dielectric) or silk or flare or (organic adj (ild dielectric interlayer))) with (oxygen or o2 or "o.sub.2"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:53
12	1341	(pattern\$ near4 photoresist) with (oxygen or o2 or "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:53

13	1786	((remov\$4 near1 portion) or pattern\$4) with photoresist with (oxygen or o2 or "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:55
14	70	(remov\$4 near1 portion) with photoresist with (oxygen or o2 or "o.sub.2")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 11:56
15	109	photoresist with (low-k or (low adj dielectric) or silk or flare) with organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:51
16	19	(low-k or (low adj dielectric) or silk or flare) adj mask\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:52
17	199	(low-k or (low adj dielectric)) near3 mask\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:52
18	48	((low-k or (low adj dielectric)) near3 mask\$4) with photoresist	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:55
19	151	((low-k or (low adj dielectric)) near3 mask\$4) not (((low-k or (low adj dielectric)) near3 mask\$4) with photoresist)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/29 12:55